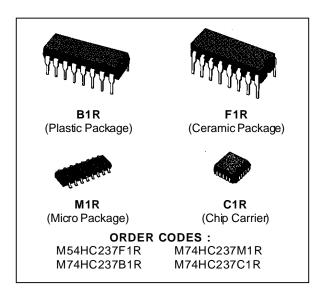


## 3 TO 8 LINE DECODER LATCH

- HIGH SPEED
- $t_{PD} = 12 \text{ ns} (TYP.) \text{ at } V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION  $I_{CC} = 4 \mu A \text{ (MAX.)} \text{ AT } I_A = 25 \text{ °C}$
- HIGH NOISE IMMUNITY

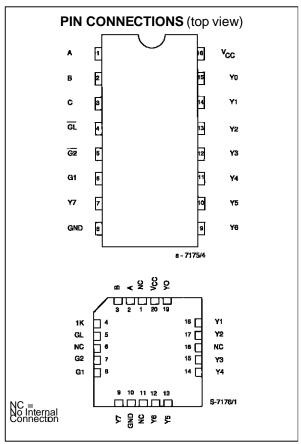
  VNIH = VNIL = 28 % VCC (MIN.)
- OUTPUT DRIVE CAPABILITY 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE | I<sub>OH</sub> | = I<sub>OL</sub> = 4 mA (MIN.)
- BALANCED PROPÄGATÍON DELAYS tplh = tphl
- WIDE OPERATING VOLTAGE RANGE Vcc (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS237



#### DESCRIPTION

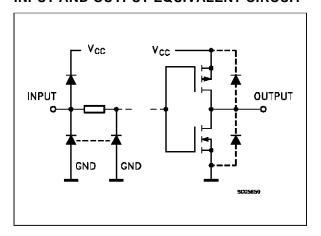
The M54/74HC237 is a high speed CMOS 3 TO 8 LINE DECODER LATCH fabricated in silicon gate C<sup>2</sup>MOS technology.

It has the same high speed performance of LSTTL combined with true CMOS low power consumption. When  $\overline{GL}$  goes from low to high, the address present at the select inputs (A, B, C) is stored in the latches. As long as  $\overline{GL}$  remains high no address changes will be recognized. Output enable controls, G1 and  $\overline{G2}$  control the state of the outputs independantly of the select or latch-enable inputs. All of the outputs are low unless G1 is high and  $\overline{G2}$  is low. The 'HC237 is ideally suited for the implementation of glitch-free decoders in stored-address applications in bus oriented systems. All inputs are equipped with protection circuits against static discharge and transient excess voltage.



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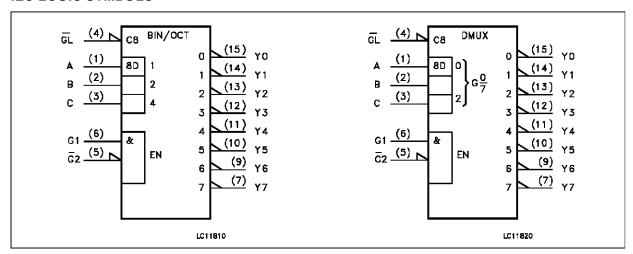
#### INPUT AND OUTPUT EQUIVALENT CIRCUIT



#### PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 2, 3	A, B, C	Data Inputs
4	lG	Latch Enable Input (Active LOW)
5	G2	Data Enable Input (Active LOW)
6	G1	Data Enable Input (Active HIGH)
15, 14, 13, 12, 11, 10, 9, 7	Y0 to Y7	Decoder Outputs
8	GND	Ground (0V)
16	Vcc	Positive Supply Voltage

#### **IEC LOGIC SYMBOLS**



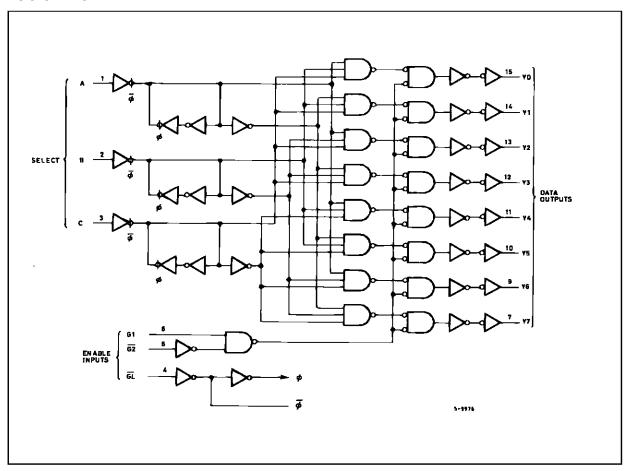
#### **TRUTH TABLE**

		INP	UTS						OUT	DIIG				
Е	NABL	E	S	ELEC	T	0011 00								
G	G2	G1	С	В	Α	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7	
Χ	Χ	L	Х	Χ	Χ	L	L	L	L	L	L	L	L	
Χ	Н	Х	Х	Χ	Χ	L	L	L	L	L	L	L	L	
L	L	Н	L	L	L	Н	L	L	L	L	L	L	L	
L	L	Н	L	L	Ι	L	Н	L	L	L	L	L	L	
L	L	Н	L	Н	L	L	L	Н	L	L	L	L	L	
L	L	Н	L	Н	Н	L	L	L	Н	L	L	L	L	
L	L	Н	Н	L	L	L	L	L	L	Н	L	L	L	
L	L	Н	Н	L	Н	L	L	L	L	L	Н	L	L	
L	L	Н	Н	Н	L	L	L	L	L	L	L	Н	L	
L	L	Н	Н	Н	Н	L	L	L	L	L	L	L	Н	
Н	L	Н	Х	Х	Х	OUTPU	OUTPUT CORRESPONDING TO STORED ADDRESS, H: ALL OTHERS, L							

X: Don't Care



### LOGIC DIAGRAM



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
$V_{I}$	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
Іок	DC Output Diode Current	± 20	mA
Io	DC Output Source Sink Current Per Output Pin	± 25	mA
Icc or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
$P_{D}$	Power Dissipation	500 (*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (\*) 500 mW:  $\cong$  65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C



### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Value	Unit	
Vcc	Supply Voltage	Supply Voltage			
$V_{I}$	Input Voltage		0 to V <sub>CC</sub>	V	
Vo	Output Voltage	0 to V <sub>CC</sub>	V		
$T_{op}$	Operating Temperature: <b>M54HC</b> Series <b>M74HC</b> Series		-55 to +125 -40 to +85	°C O°	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> = 2 V	0 to 1000	ns	
		V <sub>CC</sub> = 4.5 V	0 to 500		
		V <sub>CC</sub> = 6 V	0 to 400		

### **DC SPECIFICATIONS**

		Te	est Co	nditions				Value				
Symbol	Parameter	Vcc			$T_A = 25$ °C 54HC and 74HC			l	85 °C HC	-55 to 125 °C 54HC		Unit
		(V)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
$V_{IL}$	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	V
		6.0					1.8		1.8		1.8	
V <sub>OH</sub>	High Level	2.0	V <sub>I</sub> =		1.9	2.0		1.9		1.9		
	Output Voltage	4.5	VIH	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		
		6.0	or		5.9	6.0		5.9		5.9		V
		4.5	VIL	I <sub>O</sub> =-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I <sub>O</sub> =-5.2 mA	5.68	5.8		5.63		5.60		
$V_{OL}$	Low Level Output	2.0	Vı =			0.0	0.1		0.1		0.1	
	Voltage	4.5	VIH	I <sub>O</sub> = 20 μA		0.0	0.1		0.1		0.1	
		6.0	or			0.0	0.1		0.1		0.1	V
		4.5	V <sub>IL</sub>	lo= 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I <sub>O</sub> = 5.2 mA		0.18	0.26		0.33		0.40	
II	Input Leakage Current	6.0	V <sub>I</sub> = '	V <sub>CC</sub> or GND			±0.1		±1		±1	μΑ
Icc	Quiescent Supply Current	6.0	V <sub>I</sub> = '	V <sub>CC</sub> or GND			4		40		80	μΑ

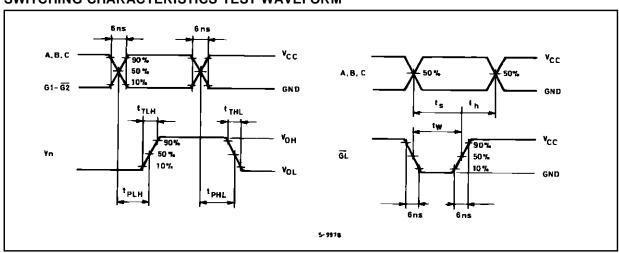


## AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ )

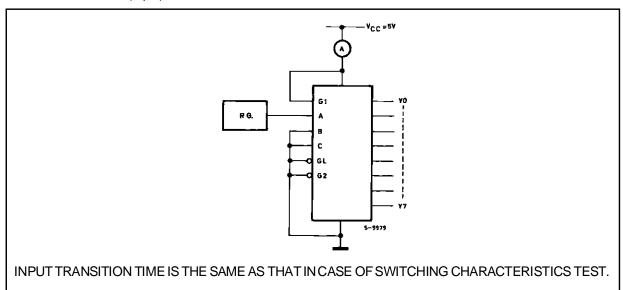
		Test Conditions				Value				
Symbol	Parameter	VCC		T <sub>A</sub> = 25 °C -40 to 85 °C 54HC and 74HC 74HC					C -55 to 125 °C 54HC	
		(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t⊤∟H	Output Transition	2.0		30	75		95		115	
$t_{THL}$	Time	4.5		8	15		19		22	ns
		6.0		7	13		16		19	
t <sub>PLH</sub>	Propagation	2.0		60	180		225		270	
t <sub>PHL</sub>	Delay Time	4.5		19	36		45		54	ns
	(A, B, C - Y)	6.0		16	31		38		46	
t <sub>PLH</sub>	Propagation	2.0		45	140		175		210	
t <sub>PHL</sub>	Delay Time	4.5		15	28		35		42	ns
(G1 - Y)	6.0		13	24		30		36		
t <sub>PLH</sub> Propagation t <sub>PHL</sub> <u>Del</u> ay Time	2.0		45	140		175		210		
	4.5		15	28		35		42	ns	
	(G2 - Y)	6.0		13	24		30		36	
t <sub>PLH</sub>	Propagation	2.0		65	190		240		285	
t <sub>PHL</sub>	Delay Time	4.5		21	38		48		57	ns
	(GL - Y)	6.0		18	32		41		48	
t <sub>W(L)</sub>	Minimum Pulse	2.0		10	75		95		110	
	Width	4.5		6	15		19		22	ns
	(GL)	6.0		6	13		16		19	
ts	Minimum Set-up	2.0		12	50		65		75	
	Time	4.5		3	10		13		15	ns
	(A, B, C - <del>GL</del> )	6.0		2	9		11		13	
t <sub>h</sub>	Minimum Hold	2.0			25		30		40	
Time	4.5			5		6		8	ns	
	(A, B, C - <del>GL</del> )	6.0			5		5		7	
CIN	Input Capacitance			5	10		10		10	pF
C <sub>PD</sub> (*)	Power Dissipation Capacitance			52						pF

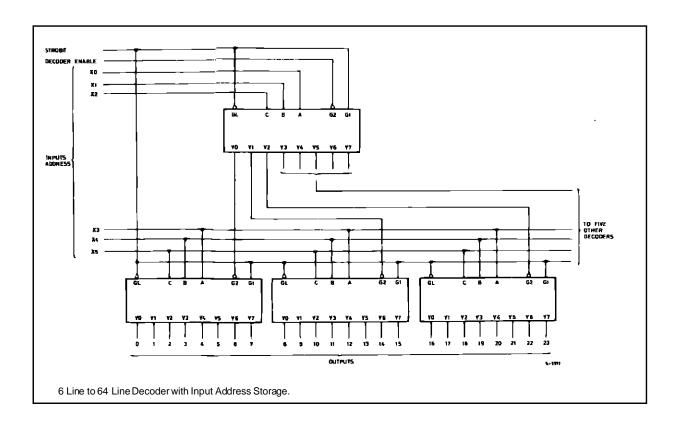
<sup>(\*)</sup> CPD is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load.

### SWITCHING CHARACTERISTICS TEST WAVEFORM



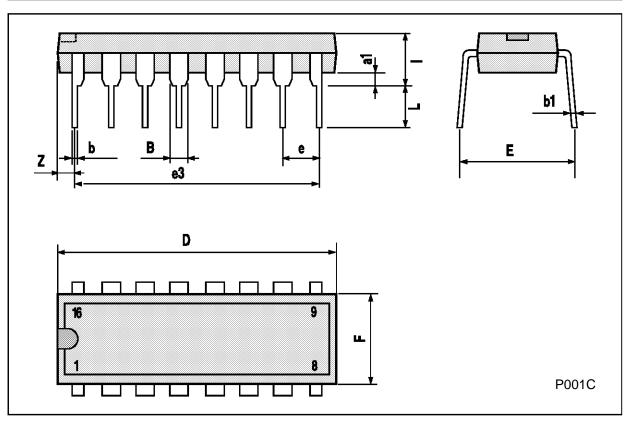
#### TEST CIRCUIT ICC (Opr.)





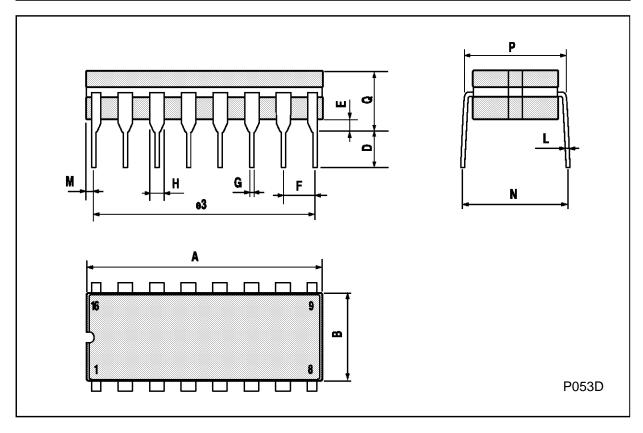
# Plastic DIP16 (0.25) MECHANICAL DATA

DIM.		mm		inch				
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
ı			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		



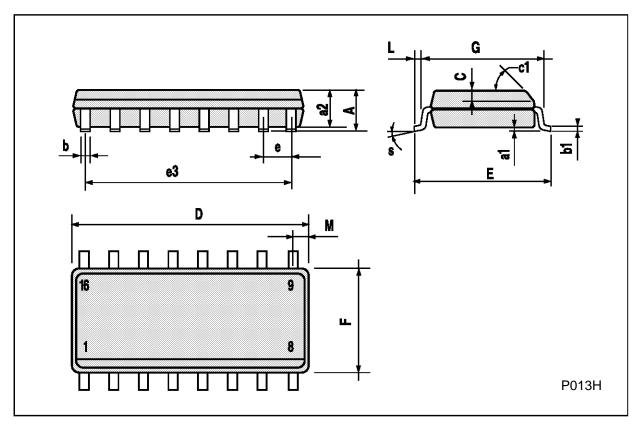
## **Ceramic DIP16/1 MECHANICAL DATA**

DIM.		mm		inch				
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			20			0.787		
В			7			0.276		
D		3.3			0.130			
Е	0.38			0.015				
e3		17.78			0.700			
F	2.29		2.79	0.090		0.110		
G	0.4		0.55	0.016		0.022		
Н	1.17		1.52	0.046		0.060		
L	0.22		0.31	0.009		0.012		
М	0.51		1.27	0.020		0.050		
N			10.3			0.406		
Р	7.8		8.05	0.307		0.317		
Q			5.08			0.200		



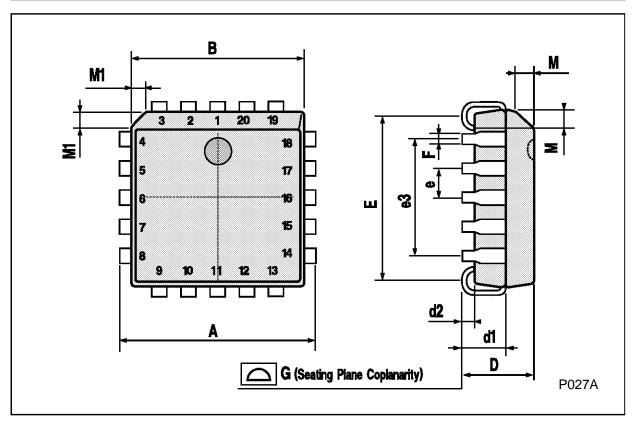
# SO16 (Narrow) MECHANICAL DATA

DIM.		mm			inch	
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
С		0.5			0.019	
c1			45°	(typ.)		
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
е		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
М			0.62			0.024
S			8° (ı	max.)		



## **PLCC20 MECHANICAL DATA**

DIM.		mm		inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		



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